

IRF6218PbF

SMPS MOSFET HEXFET® Power MOSFET

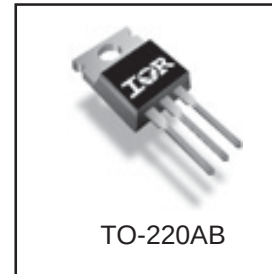
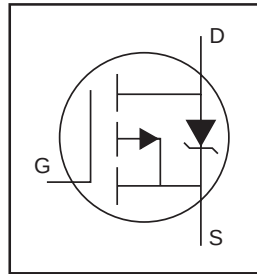
Applications

- Reset Switch for Active Clamp Reset DC-DC converters
- Lead-Free

V_{DS}	$R_{DS(on)}$ max	I_D
-150V	150mΩ@ $V_{GS} = -10V$	-27A

Benefits

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C_{OSS} to Simplify Design (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	-150	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	-27	A
I_D @ $T_C = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	-19	
I_{DM}	Pulsed Drain Current ①	-110	
P_D @ $T_C = 25^\circ C$	Maximum Power Dissipation	250	W
	Linear Derating Factor	1.6	W/°C
dv/dt	Peak Diode Recovery dv/dt ⑥	8.2	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤	—	0.61	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ⑤	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	62	

Notes ① through ④ are on page 7

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-150	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.17	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = -1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	120	150	m Ω	$V_{GS} = -10V, I_D = -16A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-3.0	—	-5.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	$V_{DS} = -120V, V_{GS} = 0V$
		—	—	-250		$V_{DS} = -120V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

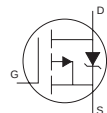
	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	11	—	—	S	$V_{DS} = -50V, I_D = -16A$
Q_g	Total Gate Charge	—	71	110	nC	$I_D = -16A$
Q_{gs}	Gate-to-Source Charge	—	21	—		$V_{DS} = -120V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	32	—		$V_{GS} = -10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	21	—	ns	$V_{DD} = -75V$
t_r	Rise Time	—	70	—		$I_D = -16A$
$t_{d(off)}$	Turn-Off Delay Time	—	35	—		$R_G = 3.9\Omega$
t_f	Fall Time	—	30	—		$V_{GS} = -10V$ ④
C_{iss}	Input Capacitance	—	2210	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	370	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	89	—		$f = 1.0MHz$
C_{oss}	Output Capacitance	—	2220	—		$V_{GS} = 0V, V_{DS} = -1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	170	—		$V_{GS} = 0V, V_{DS} = -120V, f = 1.0MHz$
$C_{oss\ eff.}$	Effective Output Capacitance	—	340	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } -120V$

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	210	mJ
I_{AR}	Avalanche Current ①	—	-16	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-27	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-110		
V_{SD}	Diode Forward Voltage	—	—	-1.6	V	$T_J = 25^\circ\text{C}, I_S = -16A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	150	—	ns	$T_J = 25^\circ\text{C}, I_F = -16A, V_{DD} = -25V$
Q_{rr}	Reverse Recovery Charge	—	860	—	nC	$di/dt = -100A/\mu s$ ④



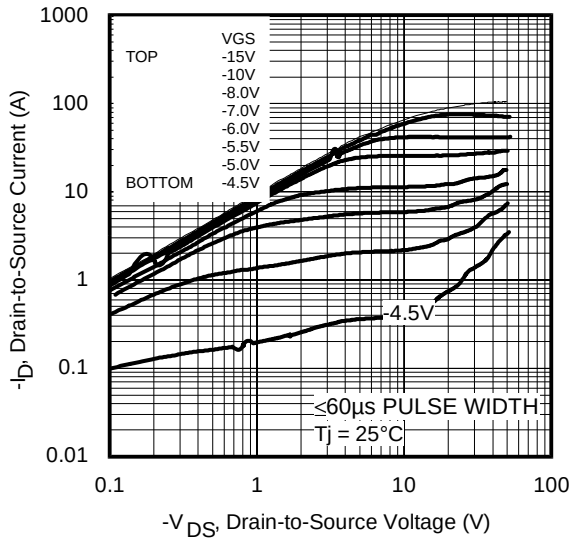


Fig 1. Typical Output Characteristics

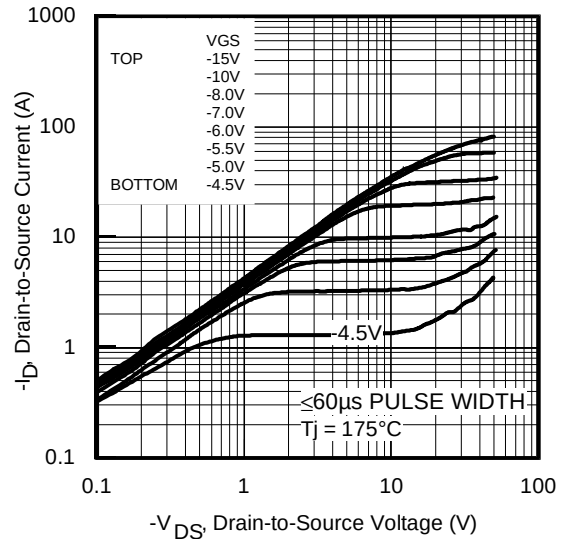


Fig 2. Typical Output Characteristics

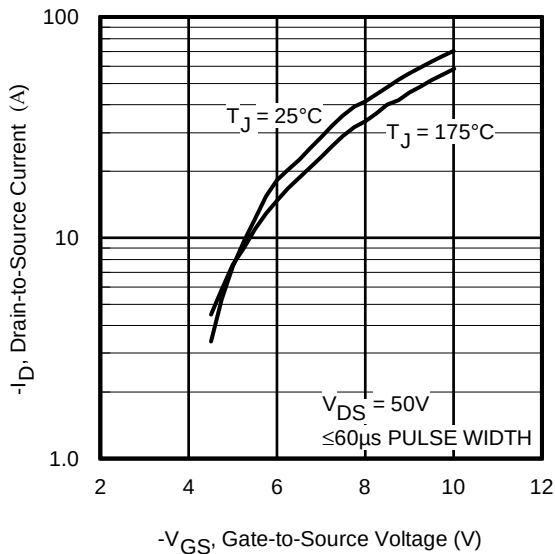


Fig 3. Typical Transfer Characteristics

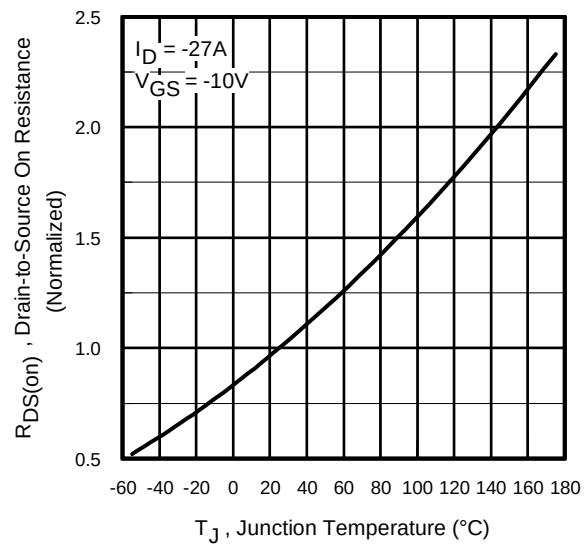


Fig 4. Normalized On-Resistance vs. Temperature

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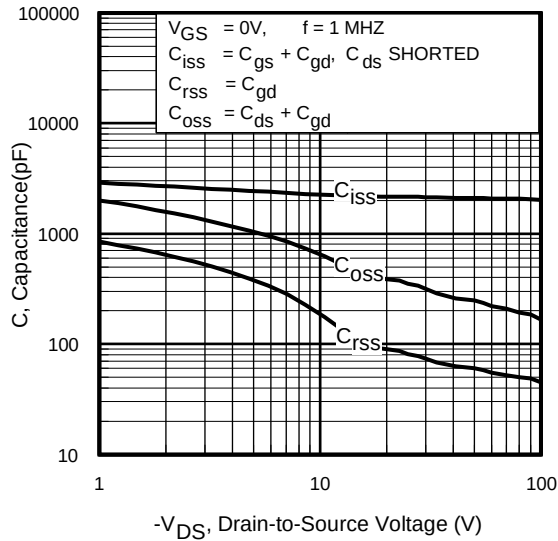


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

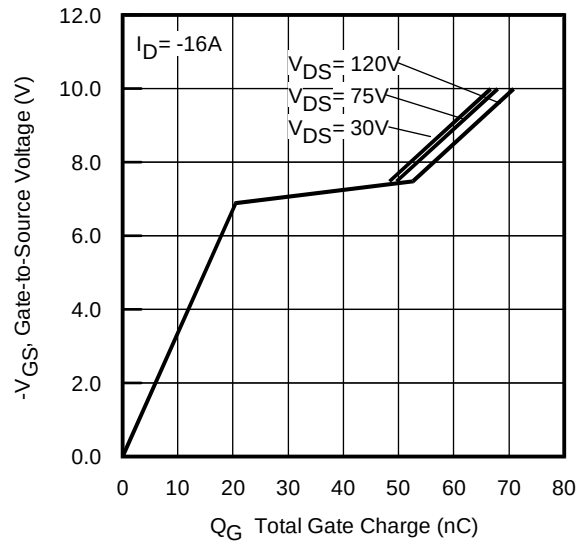


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

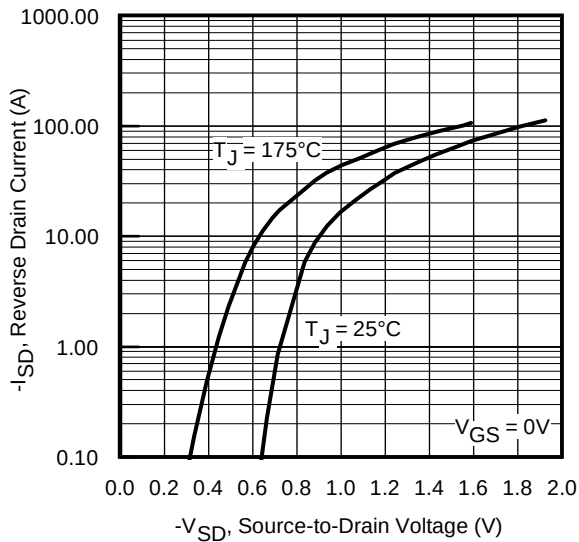


Fig 7. Typical Source-Drain Diode Forward Voltage

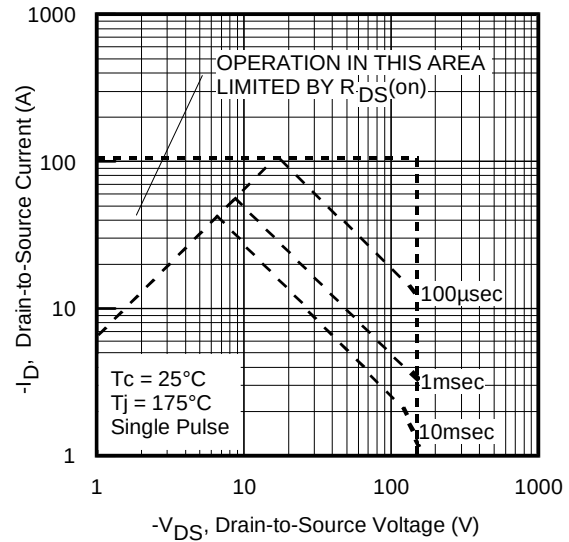


Fig 8. Maximum Safe Operating Area

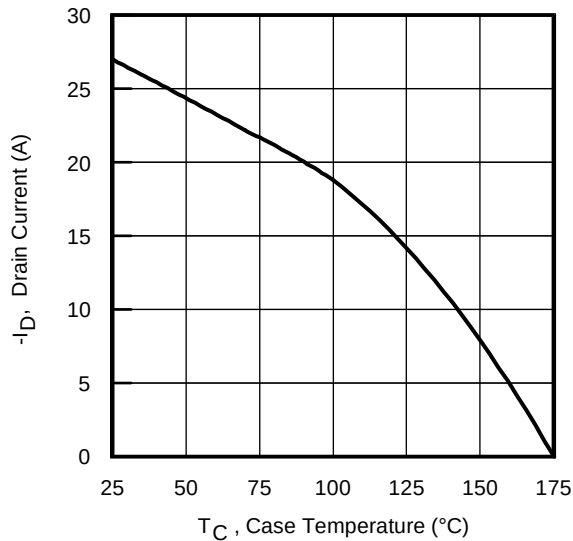


Fig 9. Maximum Drain Current vs. Ambient Temperature

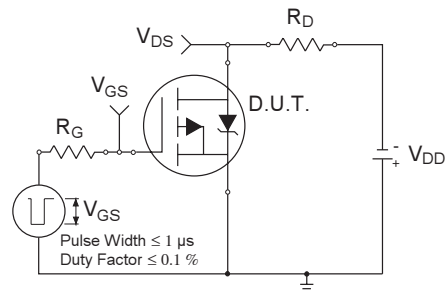


Fig 10a. Switching Time Test Circuit

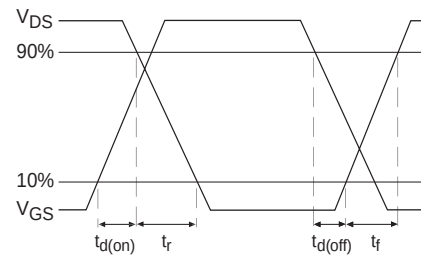


Fig 10b. Switching Time Waveforms

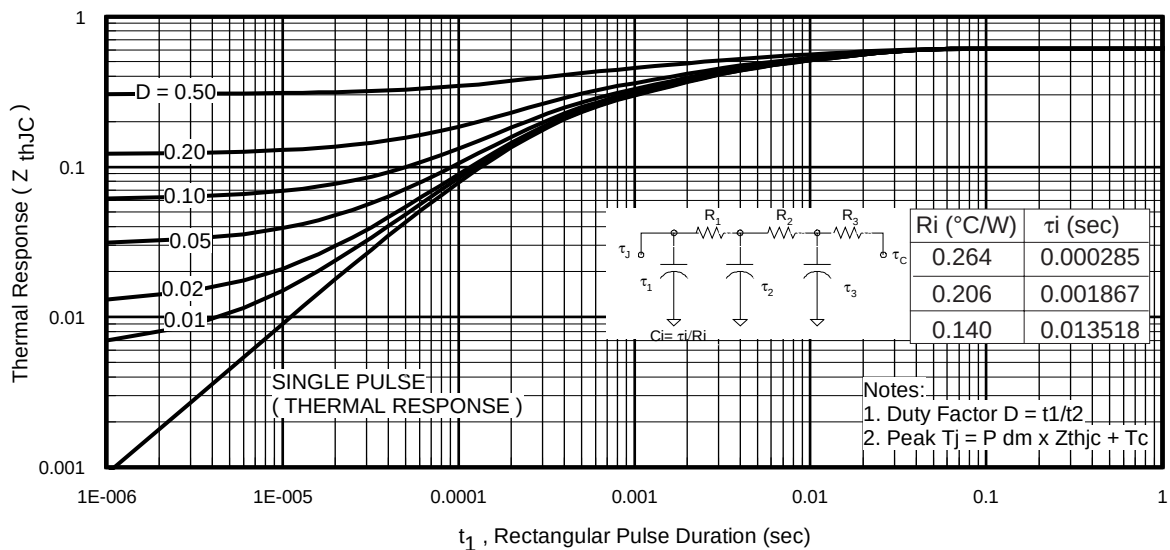


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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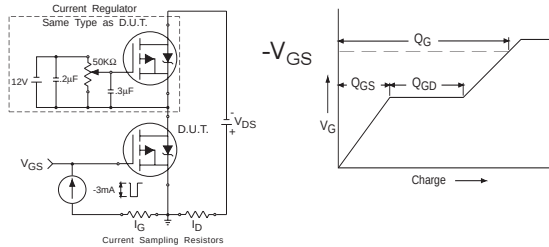
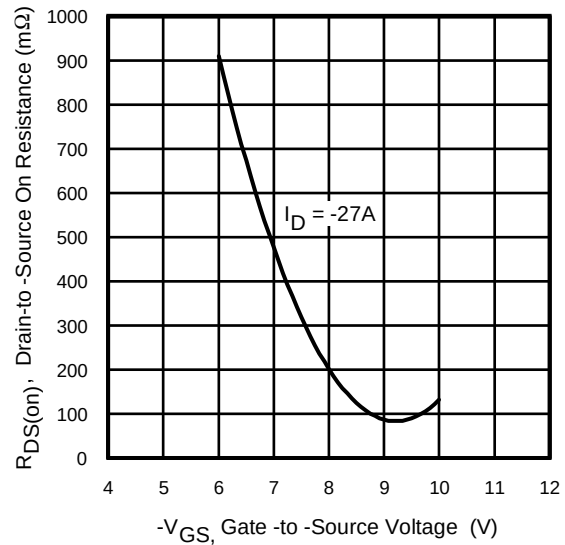
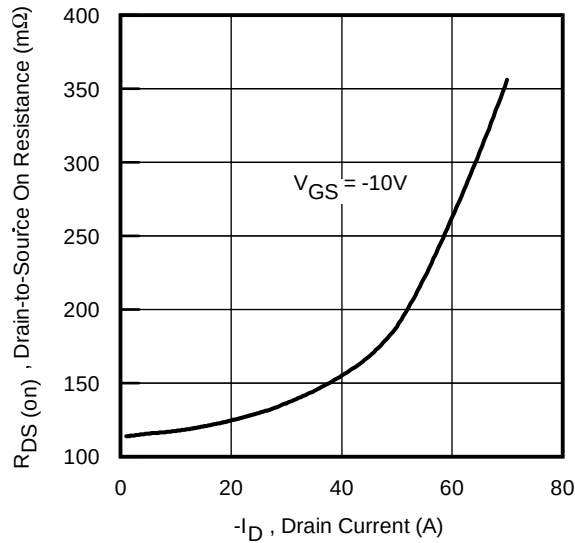


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

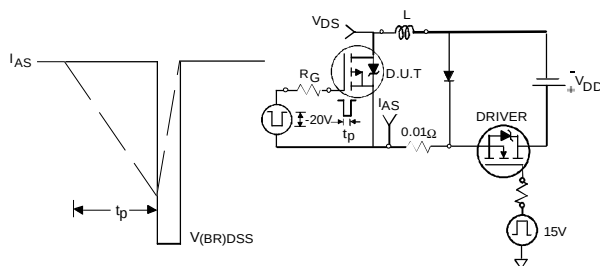


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

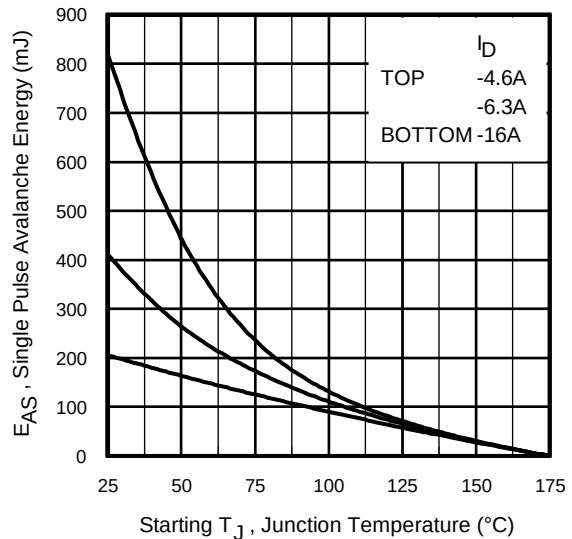
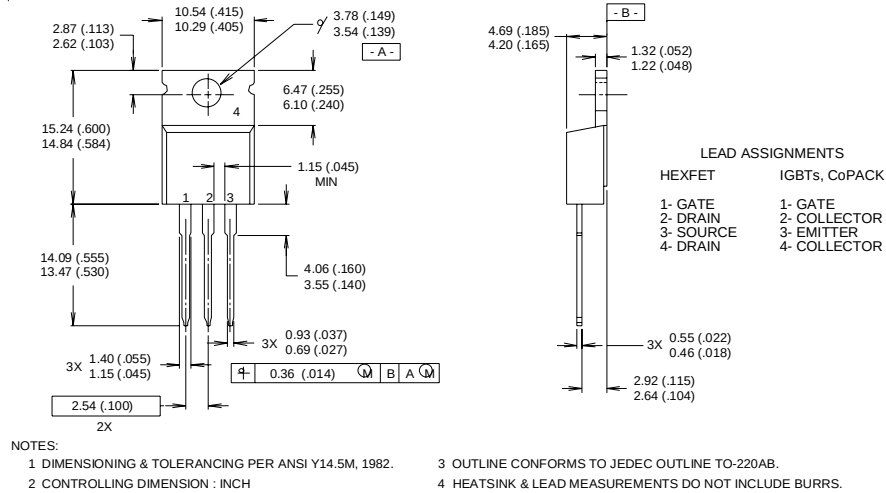


Fig 15c. Maximum Avalanche Energy vs. Drain Current

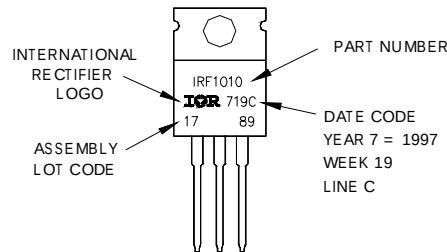
TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line position indicates "Lead-Free"



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.6\text{mH}$, $R_G = 25\Omega$, $I_{AS} = -17\text{A}$.
- ③ $I_{SD} \leq -17\text{A}$, $di/dt \leq -520\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ R_{θ} is measured at T_J of approximately 90°C .

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>

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